RECOMMEND
YJG210G06AR
FOR NEW DESIGN

N-Channel Enhancement Mode Field Effect Transistor

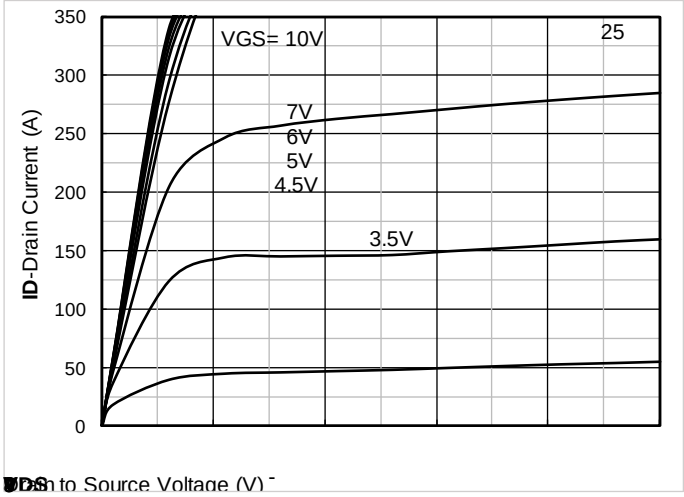
Product Summary

- V_{DS} 60V
-

■ Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250μA	60	-	-	V

Typical Electrical and Thermal Characteristics Diagrams



Figure

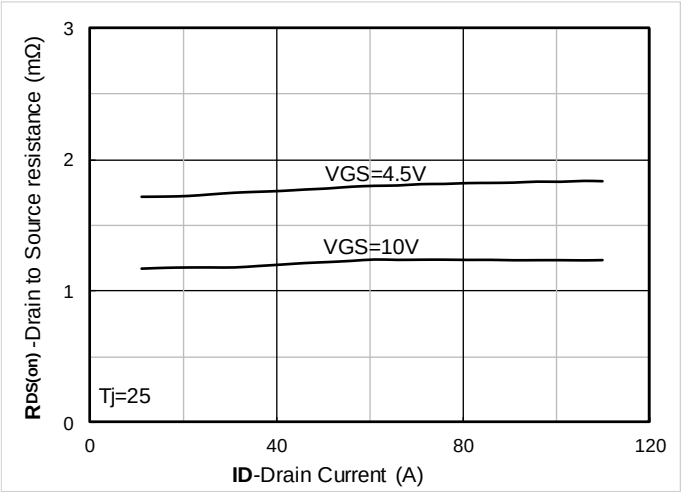


Figure 7. $R_{DS(on)}$ vs Drain Current

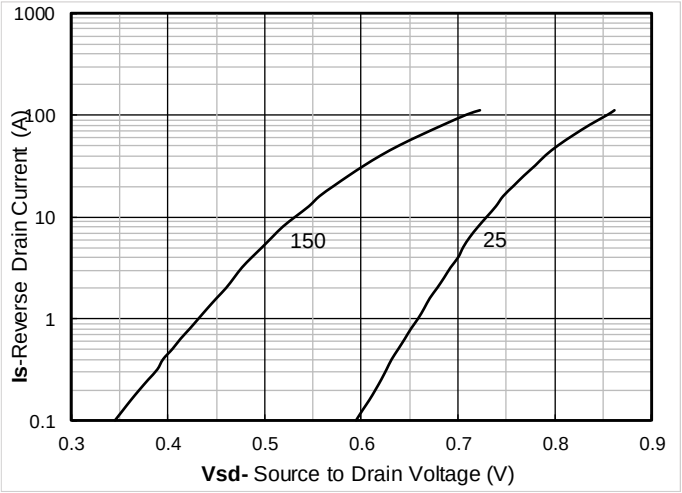


Figure 8. Forward characteristics of reverse diode

Figure 9. Normalized breakdown voltage

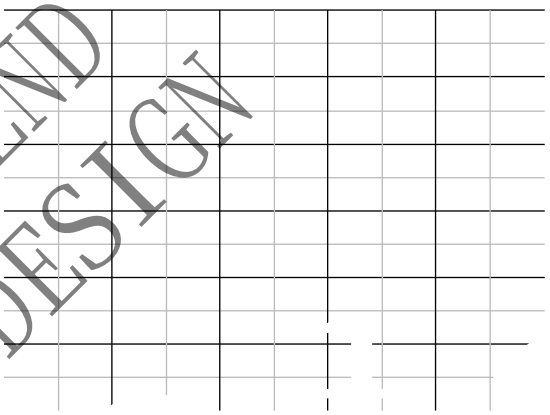


Figure 10. Normalized Threshold voltage

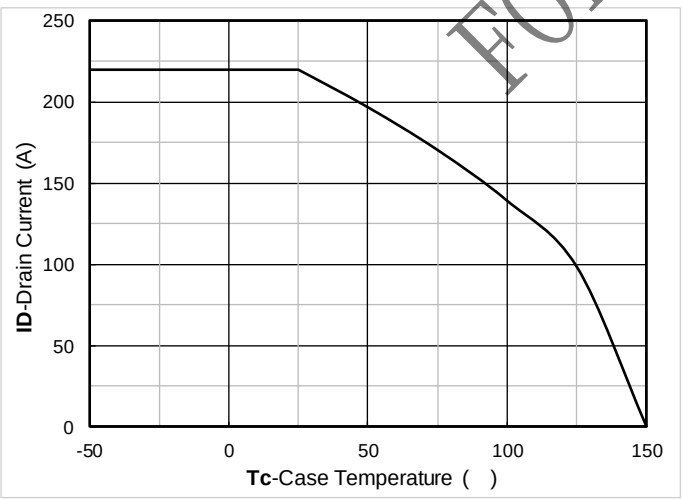


Figure 11. Current dissipation

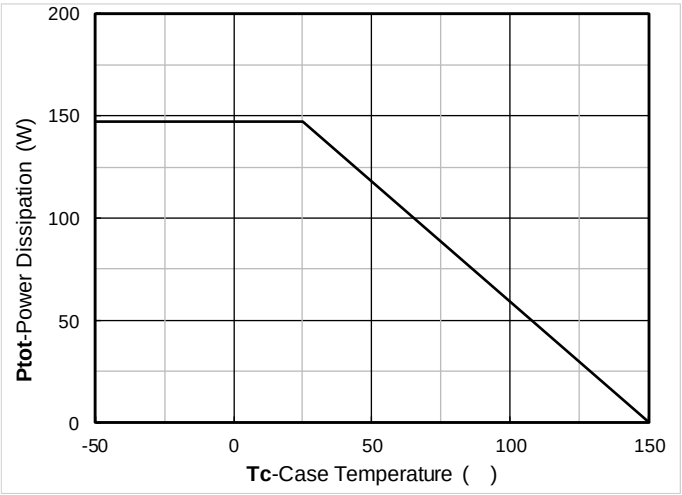


Figure 12. Power dissipation

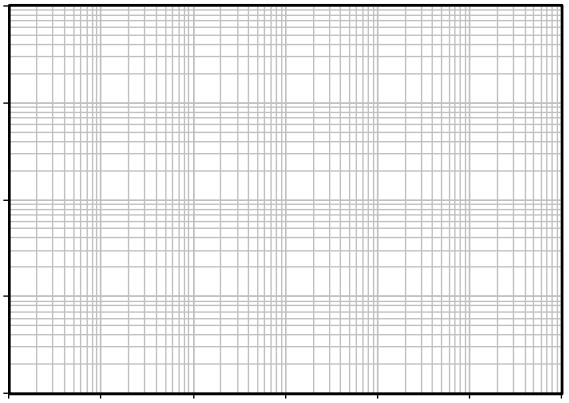


Figure 13. Maximum Transient Thermal Impedance

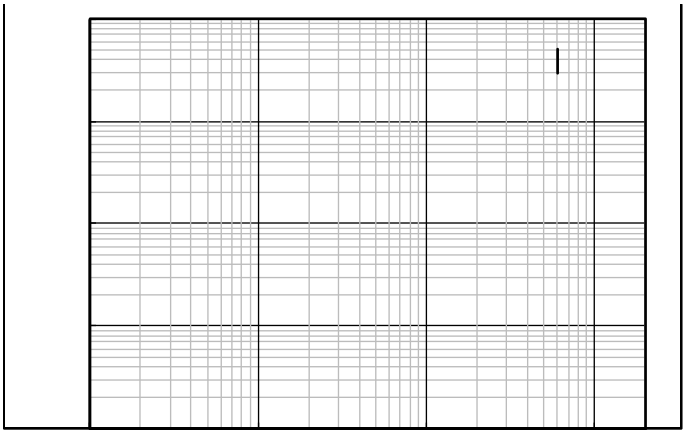


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

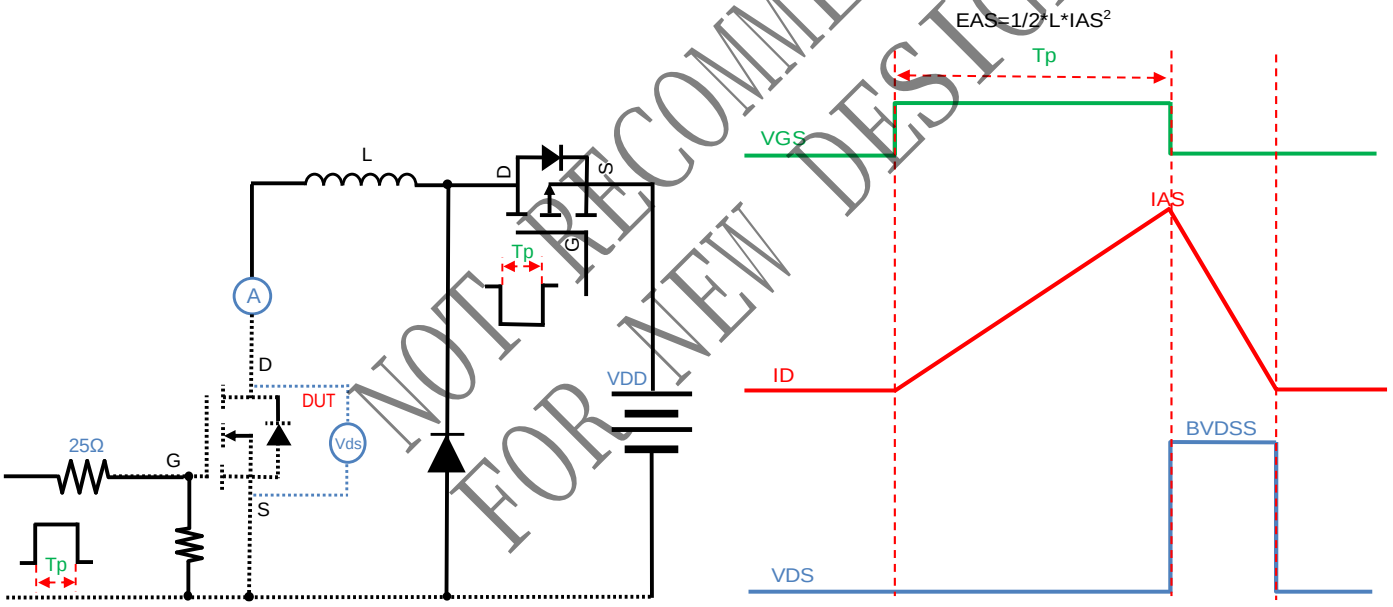


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

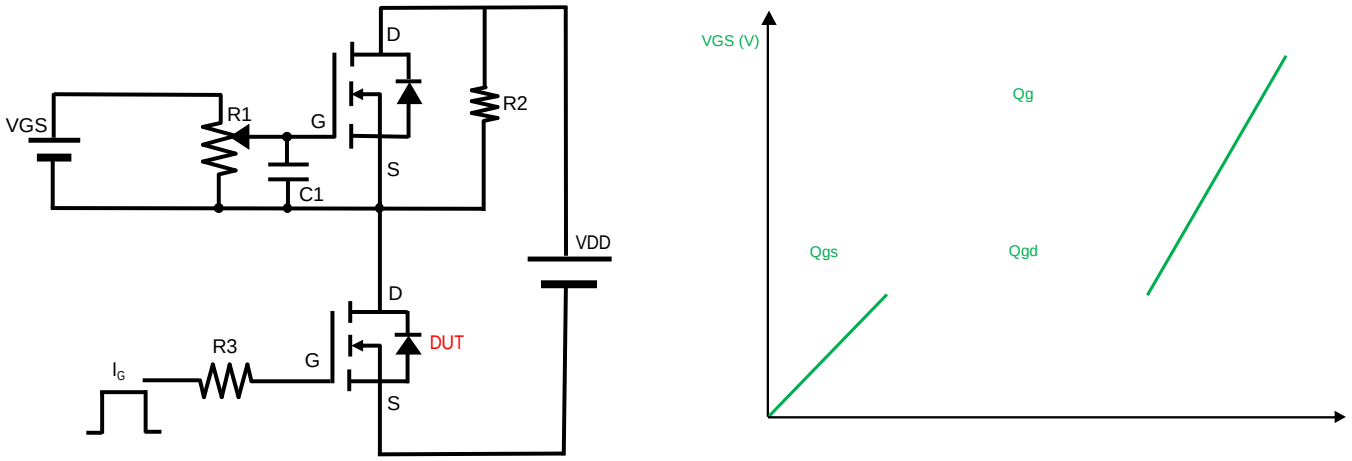


Figure B. Gate Charge Test Circuit & Waveform

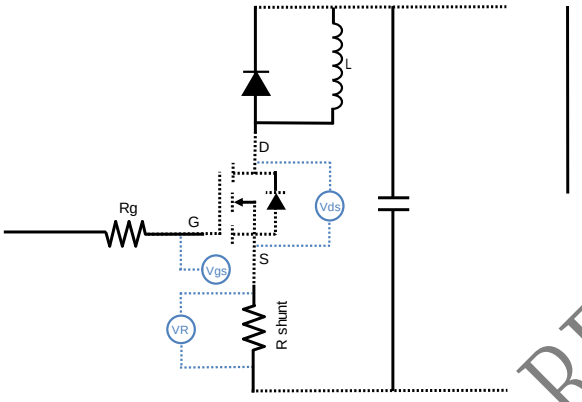


Figure C. Resistive Switching Test Circuit & Waveform

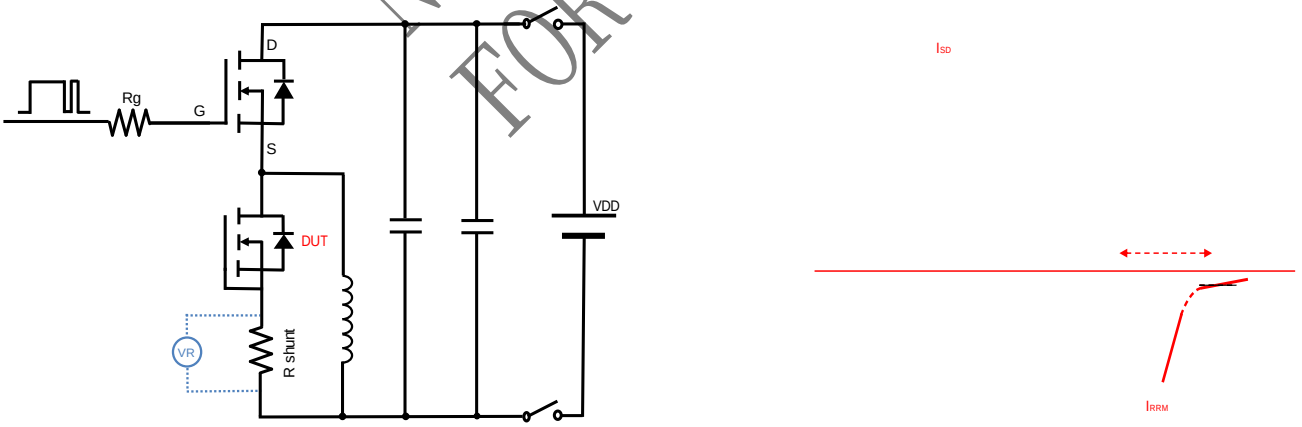
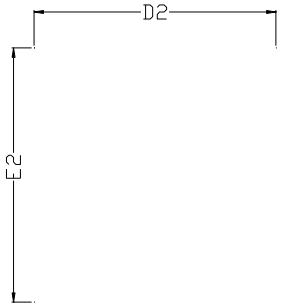


Figure D. Diode Recovery Test Circuit & Waveform

■ PDFN5060-8L-D-0.95MM Package information



Top View

Bottom View

Side View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.05	6.15
A	0.85	0.95	1.00
A1		0.203 BSC	
A2			0.08
D1	4.25	4.35	4.45
E1	3.525	3.625	3.725
D2		5.20	
E2		5.55	
L1	0.4		

Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.10mm.
3.The pad layout is for reference purposes only.

Disclaimer

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